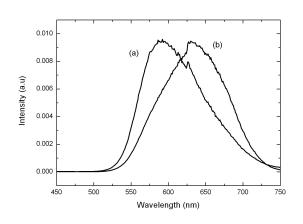
## Efficient luminescence in Eu<sup>2+</sup> activated (Ba,Ca)2Si5N8 phosphor

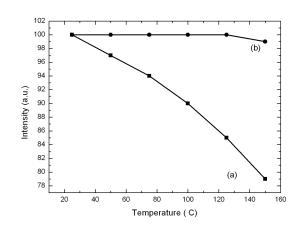
Digamber G Porob, Prasanth Kumar N, M. Satya Kishore GE Global Research, John F Welch Technology Centre, 122, Phase2, EPIP, Whitefield Road, Bangalore, India.

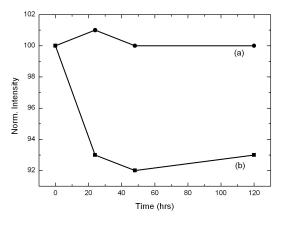
Anant A. Setlur GE Global Research, 1 Research Circle, Niskayuna, NY 12309

In this paper, we discuss luminescence properties and reliability under UV/blue flux for  $(Ba,Ca)_2Si_5N_8:Ce^{3+},Eu^{2+}.$ The barium silicon nitride known to exist in an orthorhombic crystal structure with PL emission ~580nm, whereas, the calcium silicon nitride composition crystallizes in a monoclinic crystal system with emission ~ 620nm. Partial substitution of calicum upto ~25% in Ba<sub>2</sub>Si<sub>5</sub>N<sub>8</sub> increases crystal field around Eu<sup>2</sup> ion maintaining original orthorhombic structure of Ba<sub>2</sub>Si<sub>5</sub>N<sub>8</sub>. This result in red shift of the emission position ~40nm (Figure 1). Futher, the emission of  $(Ba,Ca)_2,Si_5N_8$ at elevated temperature (upto 150°C) are more stable than their end members (Figure2). Our investigation on the stability of this material under UV/blue radiation suggest that at specific concentration levels of Ca, the host  $Ba_2Si_5N_8$  has shown better stability towards radiation damage in this system (Figure 3). We further investigate the reason for less radiation damage in (Ba,Ca)<sub>2</sub>Si<sub>5</sub>N<sub>8</sub> host compared to  $Ba_2Si_5N_8$  and nature of their emission and excitation bands at different Eu<sup>2+</sup> concentration levels.

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**Figure 3.** Integrated PL emission intensity as a function of time under,  $\lambda_{ex} = 405$  nm, for (a) (Ba,Ca)<sub>2</sub>Si<sub>5</sub>N<sub>8</sub>:Ce<sup>3+</sup>, Eu<sup>2+</sup> and (b) Ba<sub>2</sub>Si<sub>5</sub>N<sub>8</sub>:Ce<sup>3+</sup>, Eu<sup>2+</sup>